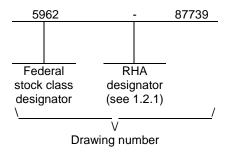
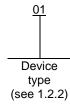
								F	REVISI	UNS										
LTR	DESCRIPTION										DA	TE (YF	R-MO-I	DA)		APPR	OVED			
А	In ac	cordan	ce with	N.O.R	. 5962	R259-	92.			d 0793				92-0	9-24			M. A.	FRYE	
В		5 with 2					•			AGE nu anges th		out.	97-06-09				R. MONNIN			
С			e to di	mensio	ns L, F	t, and F	R1 as s	pecifie	d in cas	se X ı	О			97-1	2-17			R. MO	NINIC	
D	Add r	adiatio	n hardı	ness as	ssuranc	ce requ	iremen	ts ro						98-0	6-17			R. MONNIN		
E	Add	device	ype 02	2 with ra	adiation	n hardn	ess re	quireme	ents	ro				98-1	0-29			R. MONNIN		
F	Make	chang	e to tal	ble IIB.	- ro									99-0	2-10			R. MO	NINIC	
G		ing upo			t curre	nt requ	iremen	ts. Del	ete figu	ure 1 ar	d mak	е		02-0	8-08			R. MO	NINIC	
Н	Delet	e Acce	lerated	aging										07-0	7-06			R. H	EBER	
J	Add o	device t ghout.	ype 03 - it	3 with ra	adiation	n hardn	ess re	quireme	ents. E	ditorial	chang	es		11-0	5-25			C. SA	AFFLE	
REV SHEET REV SHEET																ı	T			
	 }																			
OF SHEETS		REV STATUS REV J J J					J	J	J	J	J	J	J	J	J	J	J	J	J	
PMIC N/A PREPARED BY JOSEPH A. KERBY STANDARD MICROCIRCUIT CHECKED BY DAVID H. JOHNSON							J 1	J 2	J 3	J 4	J 5	J 6	J 7	J 8	J 9	J 10	J 11	J 12	J 13	
STA MICRO	OCIRC	CUIT		SHE PREI JO	ET PARED DSEPH	I A. KE BY	1 RBY	_				6	7 DLA I	8 -AND BUS,	9 AND OHIO	10 MAF	11 RITIMI 218-39	12 E	_	
STA MICRO DR THIS DRAWI FOR U	OCIRO AWINO ING IS A JSE BY A RTMEN NCIES O	CUIT G VAILAE ALL TS OF THE		SHE PREI JO CHEI D. APPI	PAREIDSEPHONE CKED AVID H	BY I. JOHI D BY L A. FI	1 RBY	2		MIC CO	5 SROC MPAI	co CIRCI	7 DLA I DLUM http	AND BUS, :://ww	9 AND OHICOW.ds	10 MAR O 432 cc.dla	11 RITIMI 218-39	12 E 990	13 BE	
STA MICRO DR THIS DRAWI FOR L DEPA AND AGE DEPARTME	OCIRO AWINO ING IS A JSE BY A RTMEN NCIES O	CUIT G VAILABALL TS DF THE DEFENS		SHE PREI JO CHE D. APPI M	PAREIDSEPH CKED AVID H ROVEI ICHAE	BY I. JOHI D BY L A. FI APPRO 88-0	RBY NSON RYE DVAL [2		MIC CO MO	5 SROC MPAI	CCCCIRCI	7 DLA I DLUM http	AND BUS, o://www	9 AND OHICOW.ds	MAFO 432 CC.dla	11 RITIMI 218-39 a.mil	E 990 LTAG	13 BE	

1. SCOPE

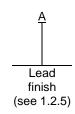
- 1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels is reflected in the PIN.
 - 1.2 PIN. The PIN is as shown in the following examples.

For device classes M and Q:

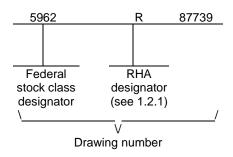


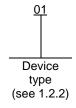


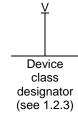


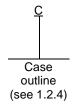


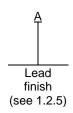
For device class V:











- 1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 <u>Device types</u>. The device types identify the circuit function as follows:

Device type	Generic number	<u>Circuit function</u>
01	LM139A	Quad voltage comparator
02	LM139	Quad voltage comparator
03	PM139A	Quad voltage comparator

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as listed below. Since the device class designator has been added after the original issuance of this drawing, device classes M and Q designators will not be included in the PIN and will not be marked on the device.

Device class	Device requirements documentation					
М	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A					
Q or V	Certification and qualification to MIL-PRF-38535					

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1.2.4 <u>Case outlines</u>. The case outlines are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
С	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14 or CDFP2-F14	4 14	Flat pack
Χ	GDFP1-G14	14	Flat pack with gull wing leads
2	CQCC1-N20	20	Square leadless chip carrier

1.2.5 <u>Lead finish</u>. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

1.3 Absolute maximum ratings. 1/

Supply voltage range (V _S)	
Input current (V _{IN} < -0.3 V)	50 mA
Maximum power dissipation (PD)	900 mW <u>2</u> /
Sink current	20 mA approximately
Lead temperature (soldering 10 seconds)	+300°C
Storage temperature range	-65°C to +150°C
Junction temperature (T _J)	+150°C
Thermal resistance, junction-to- case (θ _{JC}):	
Cases C, D, and 2	See MIL-STD-1835
Case X	23°C/W

1.4 Recommended operating conditions.

Supply voltage (V _S)	5 V dc to 30 V dc
Ambient operating temperature range (T _A)	-55°C to +125°C

1.5 Radiation features.

Device types 01, 02:

Maximum total dose available (dose rate </= 10 mrad (Si)/s...... 50 Krads(Si) 4/

^{4/} For device type 03, radiation endpoint limits for the noted parameters are guaranteed for the condition specified in MIL-STD-883, Test Method 1019, Condition D.

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Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

^{2/} Derate above 100°C ambient, 10 mW/°C.

These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions specified in MIL-STD-883, method 1019, condition A.

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at https://assist.daps.dla.mil/quicksearch/ or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.
 - 3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.
 - 3.2.3 Logic diagram. The logic diagram shall be as specified on figure 2.
- 3.2.4 Radiation exposure circuit. The radiation exposure circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing and acquiring activity upon request.
- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

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	Т	ABLE I. <u>El</u>	ectrical performance	characteristic	<u>s</u> .			
Test	Symbol	Conditions $ -55^{\circ}C \leq T_{A} \leq +125^{\circ}C $ unless otherwise specified		Group A subgroups	Device type	Limits		Unit
						Min	Max	
Input offset voltage	V _{IO}	$R_S = 0 \Omega, V_O = 1.4 V,$		1	01, 03		±2.0	mV
		+Vs = 5 \	dc to 30 V dc	2,3			±4.0	1
			M,D,P,L,R <u>1</u> / <u>2</u> /	1	01		±3.0	
			M, D, P, L <u>1</u> / <u>2/</u>	1	03			
		$R_S = 0 \Omega$	$V_{O} = 1.4 V$	1	02		±5.0	
		+V _S = 5 \	/ dc to 30 V dc	2,3			±9.0	
			M,D,P,L,R <u>1</u> / <u>2</u> /	1			±6.0	
Input offset current	I _{IO}	+l _{IN} l _{IN}	with output in	1	All		±25	nA
		the linea	ar range	2,3			±100	
			M,D,P,L,R <u>1</u> / <u>2</u> /	1				=
					01,02		±25	
	1.	l	M, D, P, L <u>1</u> / <u>2</u> /	1	03		1400	0
Input bias current	I _{IB}		+I _{IN} or -I _{IN} with output		All		±100	nA
		in the lin	lear range	2,3	04.00		±300	
			M,D,P,L,R <u>1</u> / <u>2</u> / M, D, P, L <u>1</u> / <u>2</u> /	1 1	01,02 03		±100	
Input common-mode 3/ voltage range	VICR	+V _S = 5 \	l	1,2,3	All	0	+V _S - 2.0	V
Voltage gain 3/	A _V	R _L ≥ 15 k	$R_L \ge 15 \text{ k}\Omega, +V_S = 15 \text{ V}$		All	50		V/mV
_		- , ,		2,3		25		1
Output sink current 3/	ISINK		V, +V _{IN} = 0 V, V, T _A = +25°C	1	All	6		mA
Saturation voltage	VSAT	-V _{IN} = 1 \	V, +V _{IN} = 0 V, <u>3</u> /	1	All		400	mV
		I _{SINK} ≤ 4	mA	1,2,3			700	1
		-V _{IN} = 1 \	V, +V _{IN} = 0 V,	1			400	1
		I _O = 4 mA	I _O = 4 mA				400	
			M,D,P,L,R <u>1</u> / <u>2</u> / M, D, P, L <u>1</u> / <u>2</u> /	1	01,02 03		400	
Output leakage current	l _{OL}	+V _{IN} ≥ 1	V dc, V _O = 30 V,	1	All		0.5	μА
,		-V _{IN} = 0 \	_	1,2,3			1	1
		- 114	M,D,P,L,R <u>1</u> / <u>2</u> /	1	01,02		2.5	-
			M, D, P, L <u>1/ 2/</u>		03		0.5	

See footnotes at end of table.

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TABLE I. Electrical performance characteristics.

Test	Symbol	$ \begin{array}{c} Conditions \\ -55^{\circ}C \leq T_{A} \leq +125^{\circ}C \\ unless \ otherwise \ specified \end{array} $		Group A subgroups	Device type	Limits		Unit
						Min	Max	
Supply current	Icc	$+V_S = 5 \text{ V to } 30 \text{ V},$ $R_L = \infty$		1,2,3	All		3	mA
			M,D,P,L,R <u>1</u> / <u>2</u> /	1	01, 02		2	
			M, D, P, L <u>1</u> / <u>2</u> /		03		2	
Input voltage common 3/ mode rejection ratio	CMRR	$V_{CM} = 0 V$ $R_L \ge 15 k$	V to 28 V, Ω, +V _S = 30 V	1,2,3	All	70		dB
Power supply rejection ratio	PSRR	+V _S = 5 V	/ to 30 V <u>3</u> / <u>4</u> /	1,2,3	All	70		dB
Response time 3/	^t RLH	V_{RL} = 5 V, R_L = 5.1 kΩ, 100 mV input step, T_A = +25°C		9	All		5	μs
	^t RHL	5 mV ove $T_A = +25^\circ$	•				2.5	

- Device 01 & 02 supplied to this drawing have been characterized through all levels M, D, P, L, and R of irradiation. Device 01 & 02 is only tested at the "R" level and device type 03 is only tested at "L" Level. Device 03 supplied to this drawing has been characterized through all levels P and L of irradiation. Pre and Post irradiation values are identical unless otherwise specified in table I. When performing post irradiation electrical measurements for any RHA level, TA = +25°C.
- 2/ Device types 01 and 02 may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions specified in MIL-STD-883,method 1019, condition A for device types 01 and 02. Device type 03 has been tested at a low dose rate.
- 3/ This parameter is not tested to post irradiation.
- 4/ Guaranteed, if not tested, to the limits specified in table I herein.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.
- 3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.
- 3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

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Device types	Al	LL
Case outlines	C, D, and X	2
Terminal number	Termina	l symbol
1	OUTPUT 2	NC
2	OUTPUT 1	OUTPUT 2
3	+Vs	OUTPUT 1
4	-INPUT 1	+Vs
5	+INPUT 1	NC
6	-INPUT 2	-INPUT 1
7	+INPUT 2	NC
8	-INPUT 3	+INPUT 1
9	+INPUT 3	-INPUT 2
10	-INPUT 4	+INPUT 2
11	+INPUT 4	NC
12	GND	-INPUT 3
13	OUTPUT 4	+INPUT 3
14	OUTPUT 3	-INPUT 4
15		NC
16		+INPUT 4
17		NC
18		GND
19		OUTPUT 4
20		OUTPUT 3

NC = No connection

FIGURE 1. <u>Terminal connections</u>.

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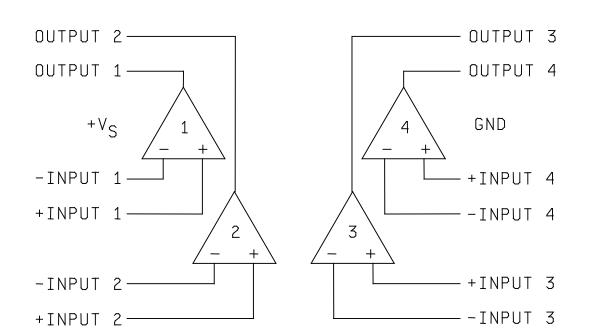


FIGURE 2. Logic diagram.

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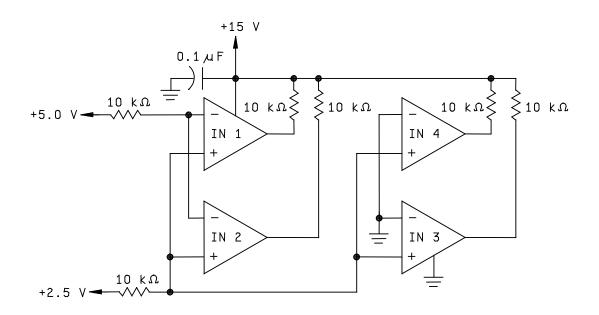


FIGURE 3. Radiation exposure circuit.

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- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M.</u> For device class M, notification to DLA Land and Maritime-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change that affects this drawing.
- 3.9 <u>Verification and review for device class M.</u> For device class M, DLA Land and Maritime, DLA Land and Maritime's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 050 (see MIL-PRF-38535, appendix A).

4. VERIFICATION

- 4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.
- 4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.
 - 4.2.1 Additional criteria for device class M.
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.
- 4.3 <u>Qualification inspection for device classes Q and V.</u> Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

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TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1	1
Final electrical parameters (see 4.2)	1, 2, 3, 9 <u>1</u> /	1, 2, 3, 9 <u>1</u> /	1, 2, 3, 9 <u>2</u> /
Group A test requirements (see 4.4)	1, 2, 3, 9	1, 2, 3, 9	1, 2, 3, 9
Group C end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3, <u>2</u> /
Group D end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3
Group E end-point electrical parameters (see 4.4)			1

^{1/} PDA applies to subgroup 1.

TABLE IIB. 240 hours and group C operating life deltas.

Test	Symbol	Device		Limits		Units
		types	Min	Max	Delta	
Input offset voltage	V _{IO}	01, 03	-2	2	±1.5	mV
		02	-5	5	±2.0	
Input bias current	I _{IB}	All	-100	100	±15	nA

^{4.4 &}lt;u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 4, 5, 6, 7, 8, 10, 11 shall be omitted.

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^{2/} Delta limits as specified in table IIB shall be required where specified, and the delta limits shall be computed with reference to the previous interim electrical parameters.

- 4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - b. $T_A = +125$ °C, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.
- 4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - 4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).
 - a. End-point electrical parameters shall be as specified in table IIA herein.
 - b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C, after exposure, to the subgroups specified in table IIA herein.
- 4.4.4.1 <u>Total dose irradiation testing</u>. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019, condition A for device types 01 and 02, condition D for device type 03 and as specified herein.
- 4.4.4.2 <u>Dose rate burnout</u>. When required by the customer test shall be performed on devices, SEC, or approved test structures at technology qualifications and after any design or process changes which may effect the RHA capability of the process. Dose rate burnout shall be performed in accordance with test method 1023 of MIL-STD-883 and as specified herein.

5. PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users should inform DLA Land and Maritime when a system application requires configuration control and which SMD's are applicable to that system. DLA Land and Maritime will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DLA Land and Maritime-VA, telephone (614) 692-0547.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-87739
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6.4 Comments. Comments on this drawing should be directed to DLA Land and Maritime-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0540. 6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331. 6.6 Sources of supply. 6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DLA Land and Maritime-VA and have agreed to this drawing. 6.6.2 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DLA Land and Maritime-VA. SIZE **STANDARD** 5962-87739 Α MICROCIRCUIT DRAWING DLA LAND AND MARITIME **REVISION LEVEL** SHEET COLUMBUS, OHIO 43218-3990

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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 11-05-25

Approved sources of supply for SMD 5962-87739 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DLA Land and Maritime -VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DLA Land and Maritime maintains an online database of all current sources of supply at http://www.dscc.dla.mil/Programs/Smcr/.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-8773901CA	01295	LM139AJB
	27014	LM139AJ-SMD
	<u>3</u> /	LM139AD/883
	<u>3</u> /	PM-139AY/883
5962-8773901DA	01295	LM139AWB
	27014	LM139AW-SMD
5962-8773901XA	27014	LM139AWG-SMD
5962-87739012A	01295	LM139AFKB
	27014	LM139AE-SMD
	<u>3</u> /	PM-139ARC/883
5962-87739012A	0C7V7	LM139LMB
5962-8773901VCA	24355	PM139AY/QMLV
5962-8773901VDA	24355	PM139AM/QMLV
5962-8773901V2A	24355	PM139ARC/QMLV
5962R8773901VCA	24355	PM139AY/QMLR
5962R8773901VDA	24355	PM139AM/QMLR
5962R8773901V2A	24355	PM139ARC/QMLR

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962R8773902VCA	24355	PM139Y/QMLR
5962R8773902VDA	24355	PM139M/QMLR
5962R8773902V2A	24355	PM139RC/QMLR
5962L8773903VDA	24355	PM139AM/QMLL

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- 2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
- 3/ Not available from an approved source of supply.

Vendor CAGEnumber_	Vendor name and address
01295	Texas Instruments, Incorporated Semiconductor Group 8505 Forest Lane P.O. Box 660199 Dallas, TX 75243 Point of contact: U.S. Highway 75 South P.O. Box 84, M/S 853 Sherman, TX 75090-9493
24355	Analog Devices, Incorporated Route 1 Industrial Park PO Box 9106 Norwood, MA 02062 Point of contact: 7910 Triad Center Drive Greensboro, NC 27409-9605
27014	National Semiconductor Corporation 2900 Semiconductor Drive P.O. Box 58090 Santa Clara, CA 95052-8090
0C7V7	E2V Aerospace and Defense, Inc. dba QP Semiconductor, Inc. 2945 Oakmead Village Court Santa Clara, CA 95051

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.